NSN 5962-01-171-7535

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-171-7535 **Body Length:** 1.290 inches **Body Width:** Between 0.500 inches and 0.610 inches **Body Height:** 0.210 inches **Maximum Power Dissipation Rating:** 575.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and burn in and bipolar and monolithic and programmable and w/enable and w/open collector **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 8 input **Case Outline Source And Designator:** D-3 mil-m-38510 **Terminal Surface Treatment:** Solder **Voltage Rating And Type Per Characteristic:** 5.5 volts power source **Time Rating Per Chacteristic:** 140.00 nanoseconds propagation delay time, low to high level output and 140.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Rom **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 24 printed circuit Shelf Life:

Demilitarization:

Unit Of Measure:

Yes - demil/mli

N/a

NSN 5962-01-171-7535

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0